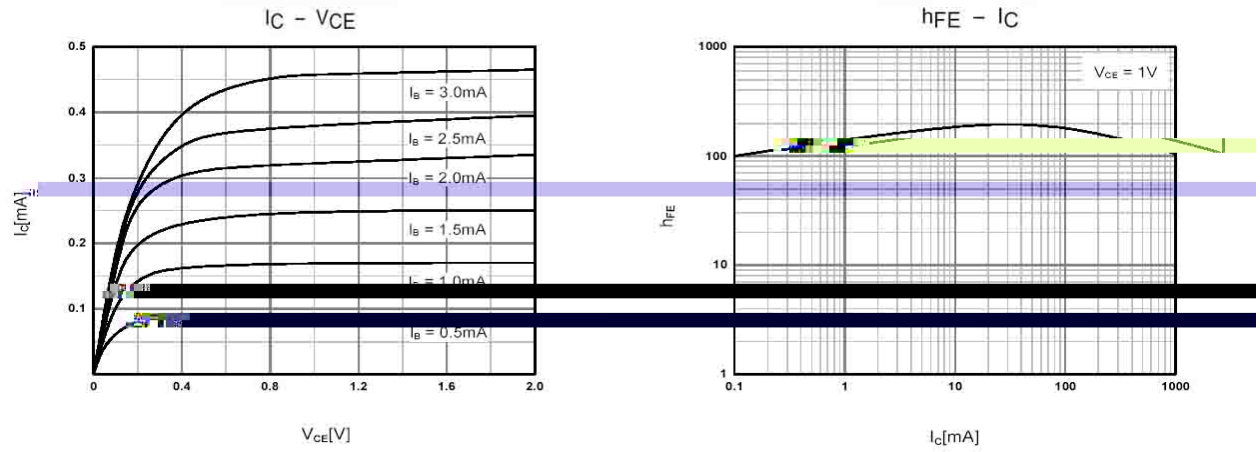
WR0<5 ḶḶÞ QSQ ÆṀч s ‖ ㄱ Silicon NPN transistor in a TO-92 Plastic Package.

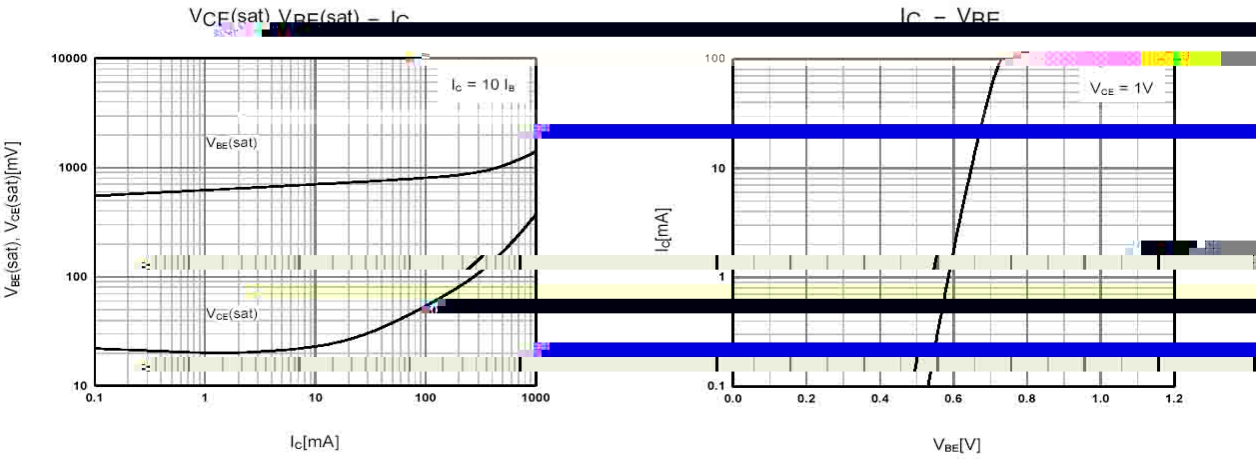
$S_{F/}$

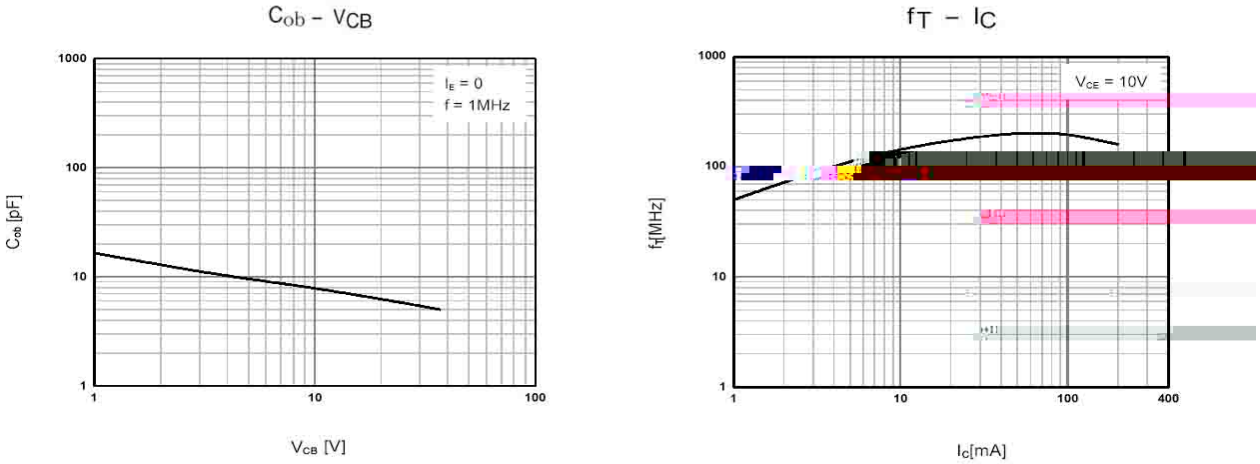
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Base Current - Continuous	I_B	500	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	‼ :ƈ ҭ Test Conditions	ѡ ṇ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=2.0mA I_B=0	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=35V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=6.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=100mA	200		350	
	$h_{FE(2)}$	V_{CE}=1.0V I_C=800mA	40			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=5.0mA	45			
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C				

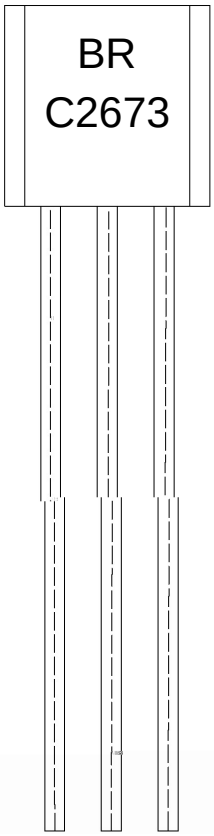
/ Electrical Characteristic Curve







/ Marking Instructions



ᄂ ᵔ χ

EU= ᵻᵡ ᵹ ᵎ ᵑᵬ

F59 : 6 χ ᵻᵡ ᵷ ᴺ ᵑᵬ

---- χ ᵻᵡ ᵻ ᶠ ᵑ̈ ᴺ ᵑᵬ ᵻ ᵩ ᵻ ᶠ ᵑ̈ ᴺ Ψ ᵖ

Note:

BR:	Company Code.
C2673:	Product Type.
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı ˋH ڑ ˋY ﾉ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ෯ ỷ ㎞ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ ˋH ڑ χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

ˇQ ţ ﾔ Ь / BULK

Package Type	Units					Dimension		(unit mm3)

ﾉ V ﾔ Ь / AMMO

Package Type	Units					Dimension	(unit mm3)

/ Notices